

# TIP140, TIP141, TIP142, (NPN); TIP145, TIP146, TIP147, (PNP)

TIP141, TIP142, TIP146, and TIP147 are Preferred Devices

## Darlington Complementary Silicon Power Transistors

Designed for general-purpose amplifier and low frequency switching applications.

### Features

- High DC Current Gain –  
 $\text{Min } h_{FE} = 1000 @ I_C$   
 $= 5.0 \text{ A, } V_{CE} = 4 \text{ V}$
- Collector–Emitter Sustaining Voltage – @ 30 mA  
 $V_{CEO(sus)} = 60 \text{ Vdc (Min) – TIP140, TIP145}$   
 $= 80 \text{ Vdc (Min) – TIP141, TIP146}$   
 $= 100 \text{ Vdc (Min) – TIP142, TIP147}$
- Monolithic Construction with Built–In Base–Emitter Shunt Resistor
- Pb–Free Packages are Available\*

### MAXIMUM RATINGS

Rating	Symbol	TIP140 TIP145	TIP141 TIP146	TIP142 TIP147	Unit
Collector – Emitter Voltage	$V_{CEO}$	60	80	100	Vdc
Collector – Base Voltage	$V_{CB}$	60	80	100	Vdc
Emitter – Base Voltage	$V_{EB}$	5.0			Vdc
Collector Current	$I_C$				Adc
– Continuous		10			
– Peak (Note 1)		15			
Base Current – Continuous	$I_B$	0.5			Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	125			W
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +150			$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	1.0	$^\circ\text{C/W}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	35.7	$^\circ\text{C/W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. 5 ms,  $\leq 10\%$  Duty Cycle.

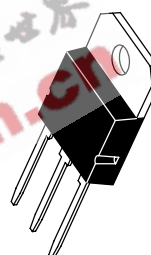
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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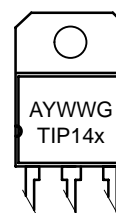
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**10 AMPERE  
DARLINGTON  
COMPLEMENTARY SILICON  
POWER TRANSISTORS  
60–100 VOLTS, 125 WATTS**



SOT–93 (TO–218)  
CASE 340D  
STYLE 1

### MARKING DIAGRAM



A = Assembly Location  
 Y = Year  
 WW = Work Week  
 TIP14x = Device Code  
 x = 0, 1, 2, 5, 6, or 7  
 G = Pb–Free Package

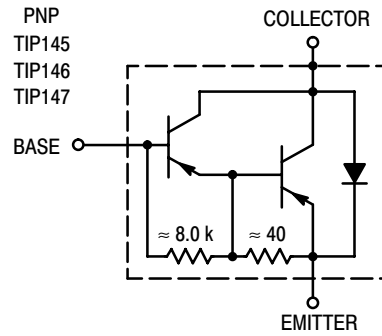
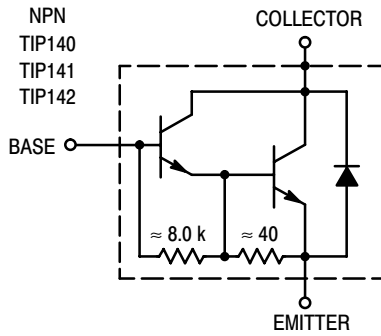
### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

# TIP140, TIP141, TIP142, (NPN); TIP145, TIP146, TIP147, (PNP)

## DARLINGTON SCHEMATICS



## ORDERING INFORMATION

Device	Package	Shipping
TIP140	SOT-93 (TO-218)	30 Units / Rail
TIP140G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP141	SOT-93 (TO-218)	30 Units / Rail
TIP141G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP142	SOT-93 (TO-218)	30 Units / Rail
TIP142G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP145	SOT-93 (TO-218)	30 Units / Rail
TIP145G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP146	SOT-93 (TO-218)	30 Units / Rail
TIP146G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP147	SOT-93 (TO-218)	30 Units / Rail
TIP147G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail

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## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Sustaining Voltage (Note 2) ( $I_C = 30\text{ mA}$ , $I_B = 0$ )	$V_{CE(sus)}$	60 80 100	– – –	– – –	Vdc
Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 40\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 50\text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	– – –	– – –	2.0 2.0 2.0	mA
Collector Cutoff Current ( $V_{CB} = 60\text{ V}$ , $I_E = 0$ ) ( $V_{CB} = 80\text{ V}$ , $I_E = 0$ ) ( $V_{CB} = 100\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	– – –	– – –	1.0 1.0 1.0	mA
Emitter Cutoff Current ( $V_{BE} = 5.0\text{ V}$ )	$I_{EBO}$	–	–	2.0	mA

## ON CHARACTERISTICS (Note 2)

DC Current Gain ( $I_C = 5.0\text{ A}$ , $V_{CE} = 4.0\text{ V}$ ) ( $I_C = 10\text{ A}$ , $V_{CE} = 4.0\text{ V}$ )	$h_{FE}$	1000 500	– –	– –	–
Collector–Emitter Saturation Voltage ( $I_C = 5.0\text{ A}$ , $I_B = 10\text{ mA}$ ) ( $I_C = 10\text{ A}$ , $I_B = 40\text{ mA}$ )	$V_{CE(sat)}$	– –	– –	2.0 3.0	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10\text{ A}$ , $I_B = 40\text{ mA}$ )	$V_{BE(sat)}$	–	–	3.5	Vdc
Base–Emitter On Voltage ( $I_C = 10\text{ A}$ , $V_{CE} = 4.0\text{ Vdc}$ )	$V_{BE(on)}$	–	–	3.0	Vdc

## SWITCHING CHARACTERISTICS

Resistive Load (See Figure 1)						
Delay Time	$(V_{CC} = 30\text{ V}$ , $I_C = 5.0\text{ A}$ , $I_B = 20\text{ mA}$ , Duty Cycle $\leq 2.0\%$ , $I_{B1} = I_{B2}$ , $R_C$ & $R_B$ Varied, $T_J = 25^\circ\text{C}$ )	$t_d$	–	0.15	–	$\mu\text{s}$
Rise Time		$t_r$	–	0.55	–	$\mu\text{s}$
Storage Time		$t_s$	–	2.5	–	$\mu\text{s}$
Fall Time		$t_f$	–	2.5	–	$\mu\text{s}$

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

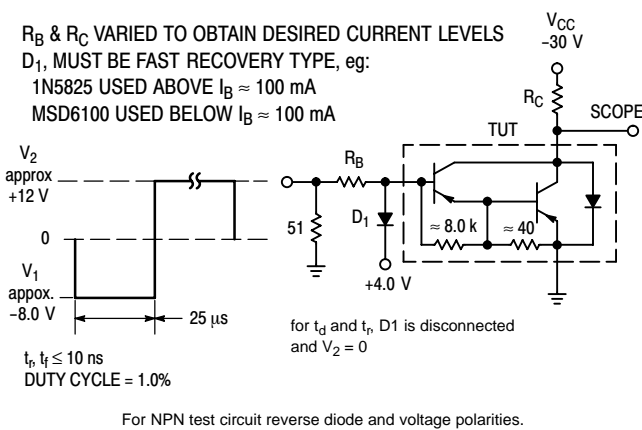


Figure 1. Switching Times Test Circuit

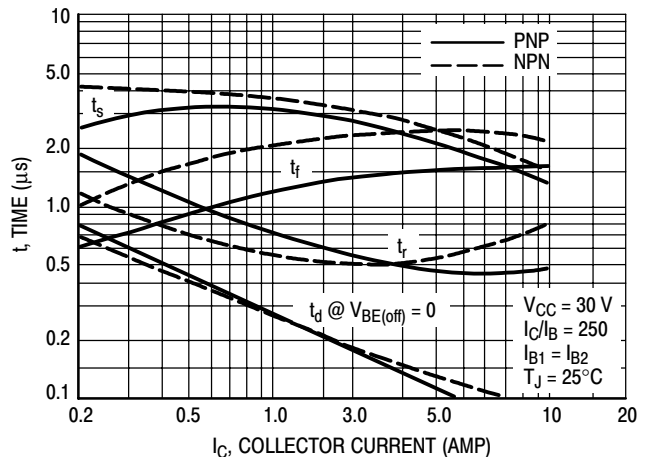


Figure 2. Switching Times

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## TYPICAL CHARACTERISTICS

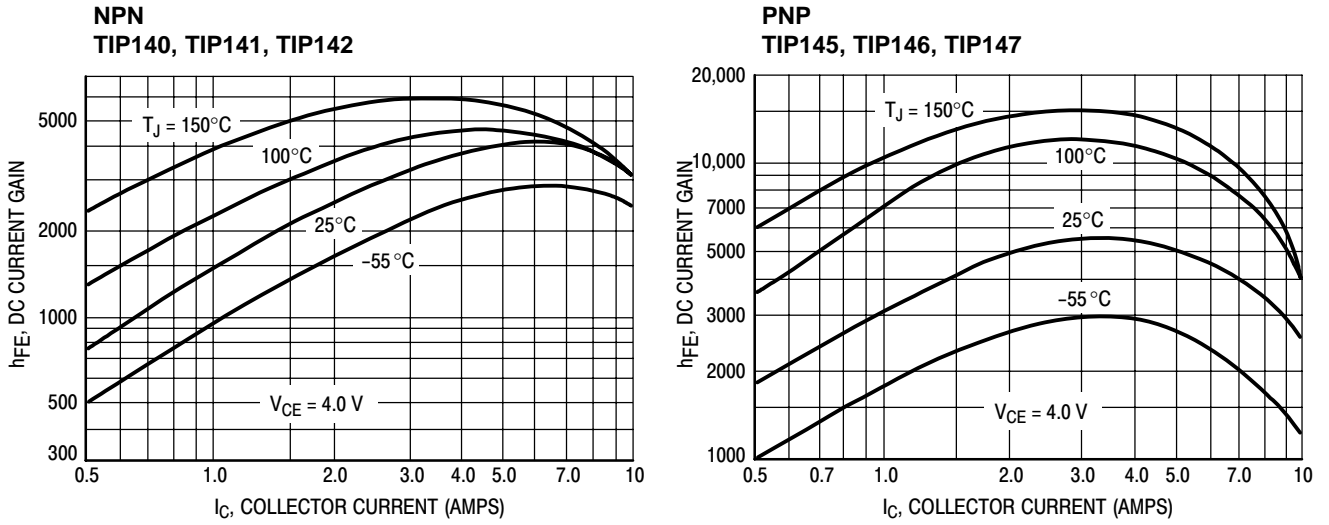


Figure 3. DC Current Gain versus Collector Current

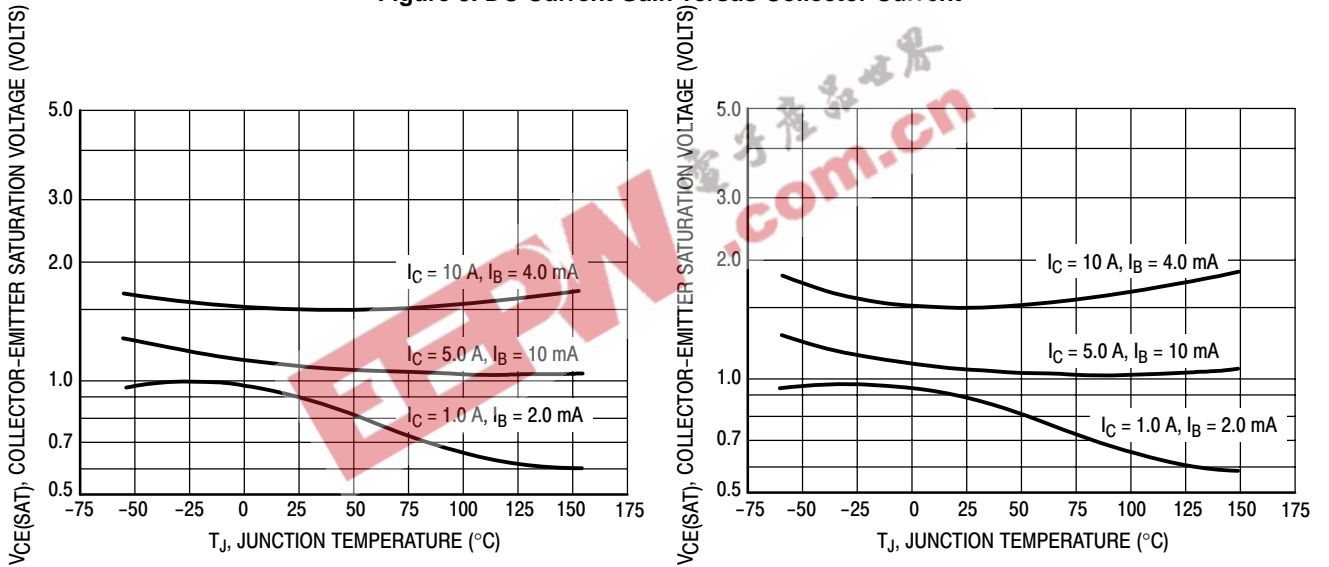


Figure 4. Collector-Emitter Saturation Voltage

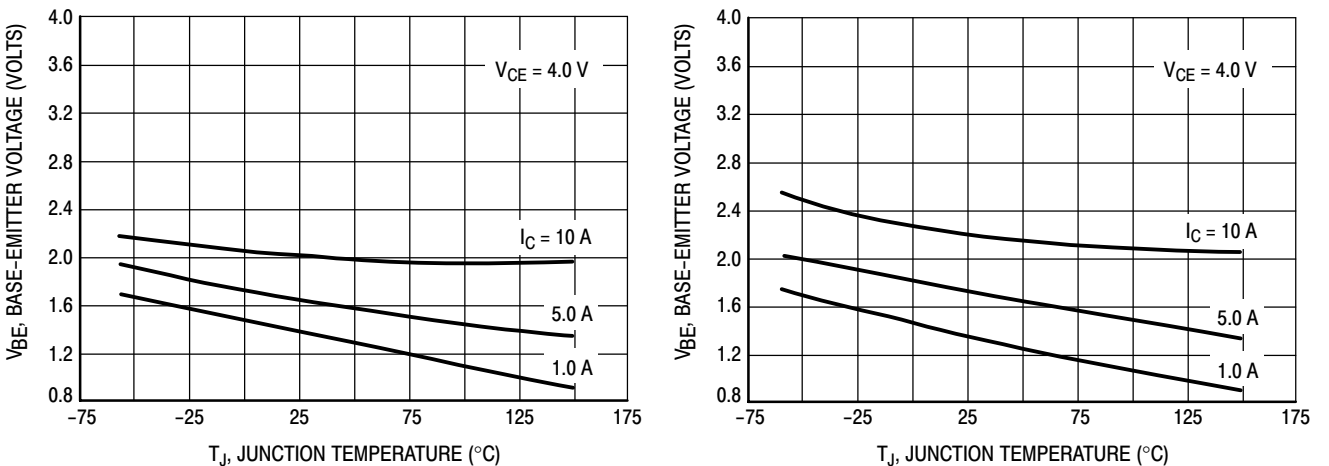


Figure 5. Base-Emitter Voltage

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## ACTIVE-REGION SAFE OPERATING AREA

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

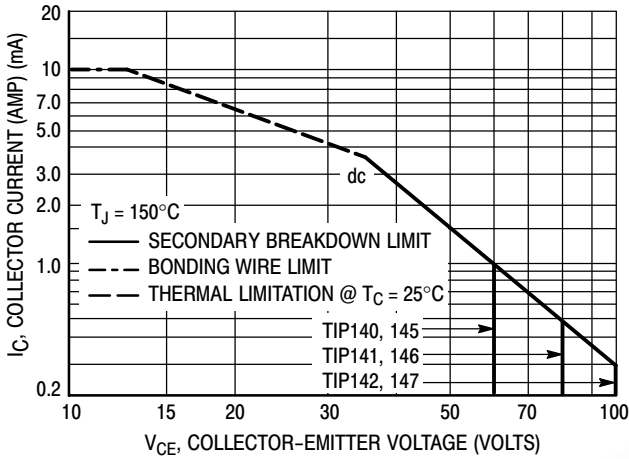


Figure 6. Active-Region Safe Operating Area

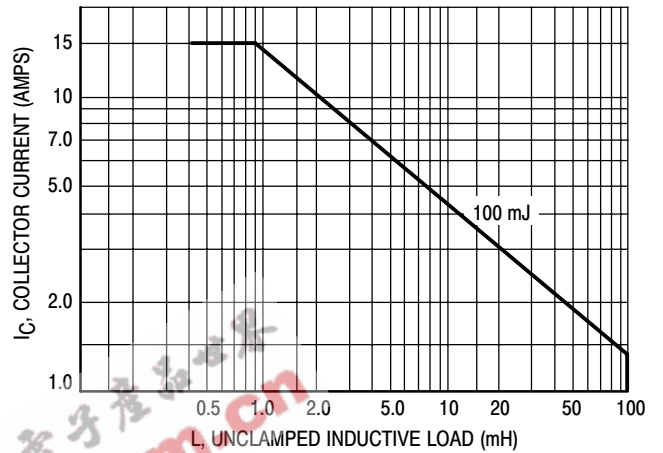
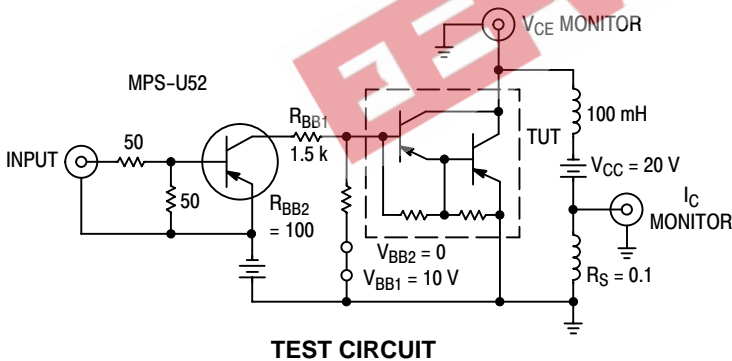
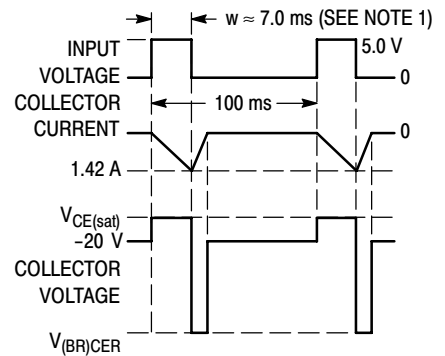


Figure 7. Unclamped Inductive Load



TEST CIRCUIT

NOTE 1: Input pulse width is increased until  $I_{CM} = 1.42\text{ A}$ .  
NOTE 2: For NPN test circuit reverse polarities.



VOLTAGE AND CURRENT WAVEFORMS

Figure 8. Inductive Load

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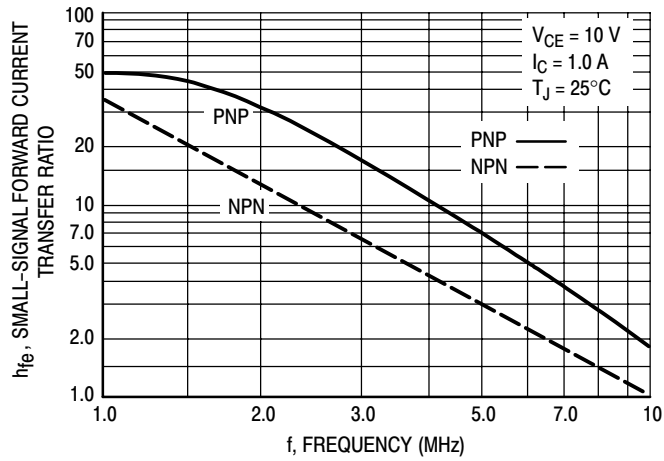


Figure 9. Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio

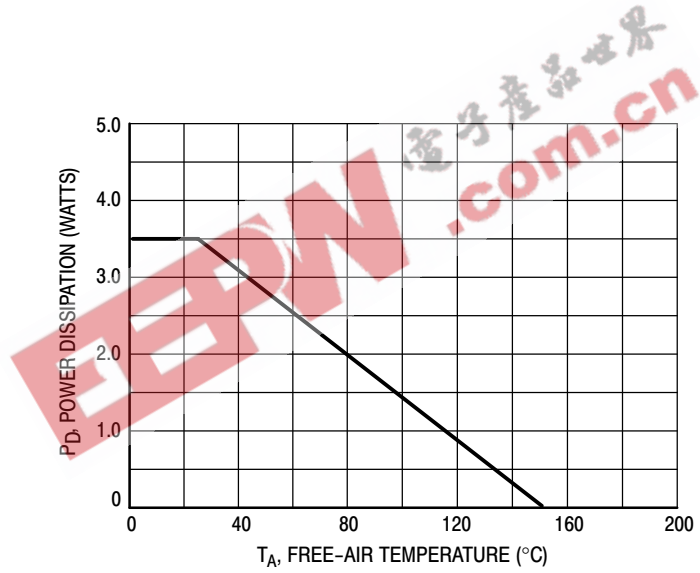
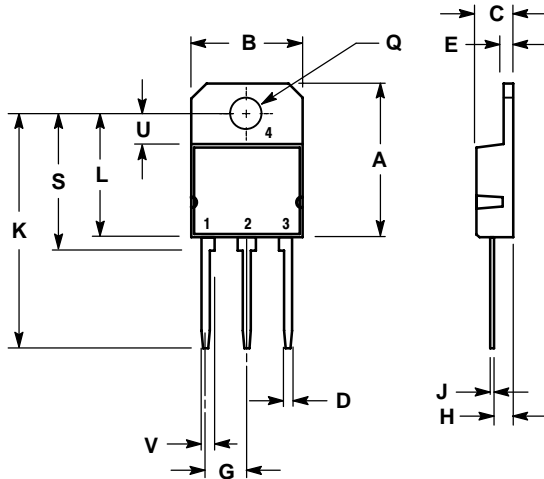


Figure 10. Free-Air Temperature Power Derating

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## PACKAGE DIMENSIONS


SOT-93 (TO-218)  
CASE 340D-02  
ISSUE E



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

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